

30V(D-S) N-Channel Enhancement Mode Power MOS FET

General Features

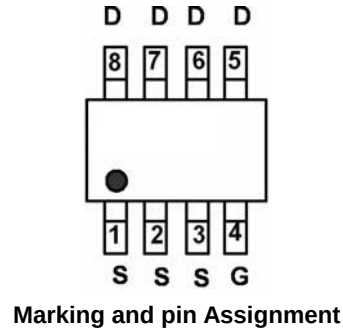
- $V_{DS} = 30V, I_D = 18A$
 $R_{DS(ON)} < 7m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 10m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized Avalanche voltage and current



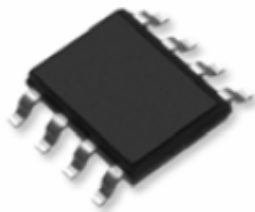
Lead Free

Application

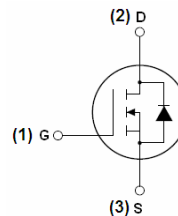
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



PIN Configuration



SOP-8 top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MSN0318W	MSN0318W	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	18	A
Drain Current-Continuous($T_A=100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	12.7	A
Pulsed Drain Current	I_{DM}	48	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	42	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

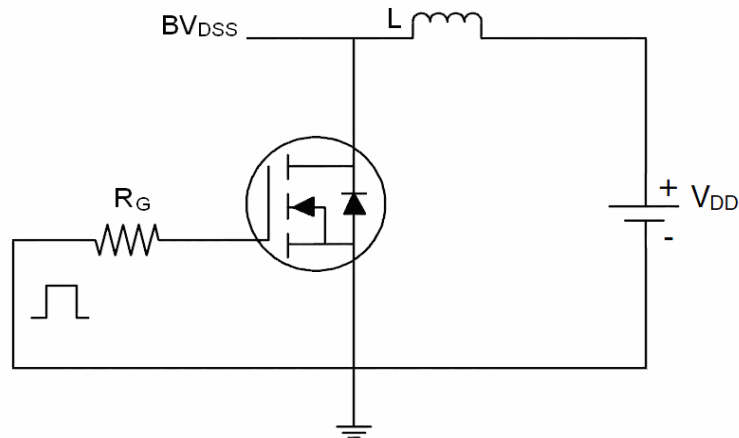
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.9	1.1	1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	5.5	7	mΩ
		V _{GS} =4.5V, I _D =10A	-	6.5	10	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =12A	5	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C _{OSS}		-	460	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	230	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,I _D =12A V _{GS} =10V,R _{GEN} =2.7Ω	-	20	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	60	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =12A, V _{GS} =10V	-	41	-	nC
Gate-Source Charge	Q _{gs}		-	14	-	nC
Gate-Drain Charge	Q _{gd}		-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	18	A

Notes:

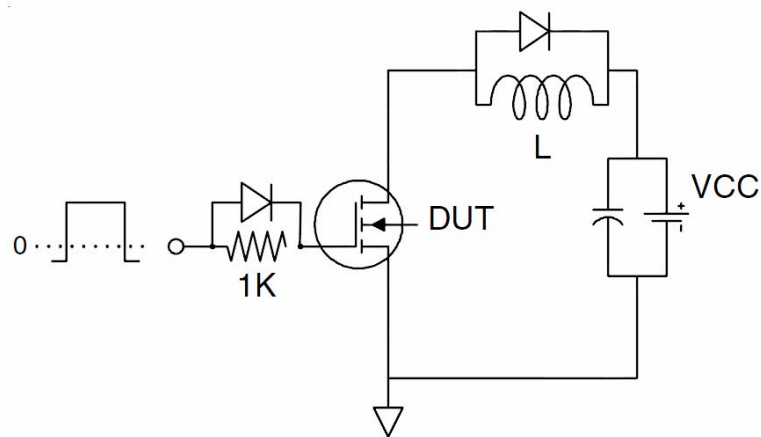
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

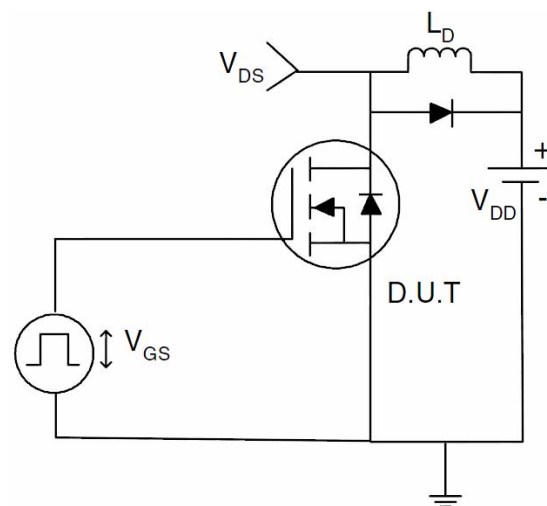
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

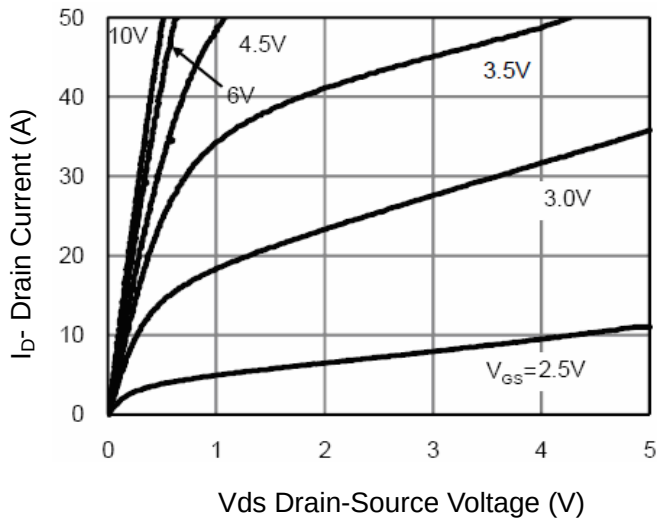


Figure 1 Output Characteristics

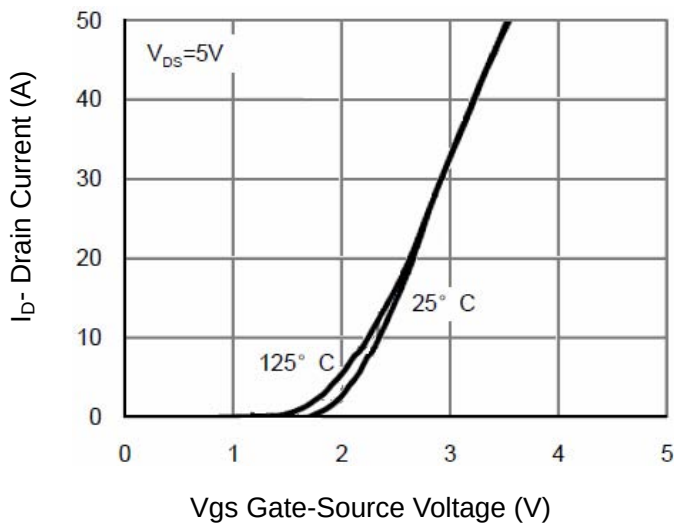


Figure 2 Transfer Characteristics

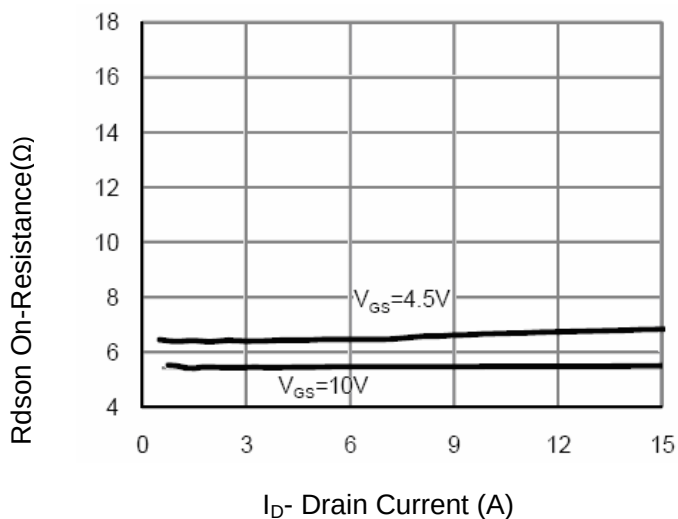


Figure 3 $R_{DS(on)}$ - Drain Current

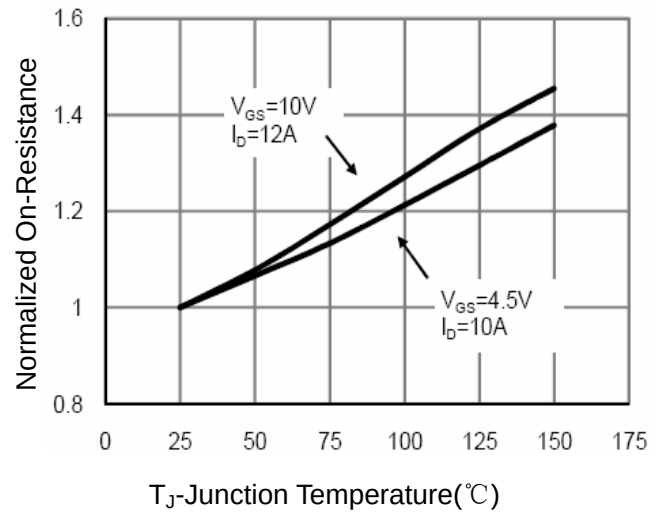


Figure 4 $R_{DS(on)}$ -Junction Temperature

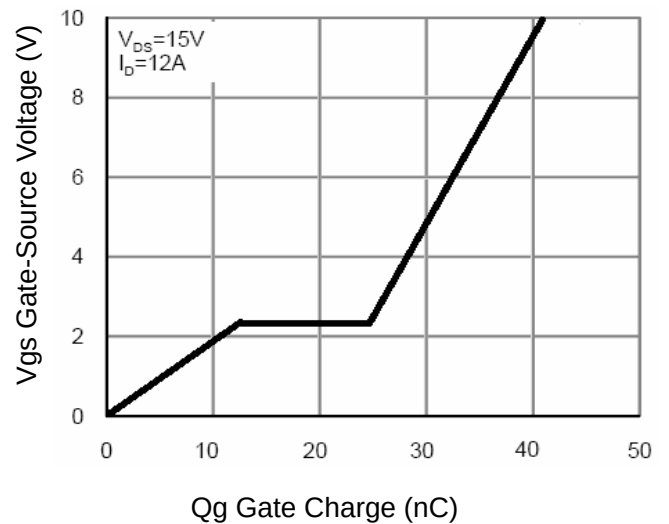


Figure 5 Gate Charge

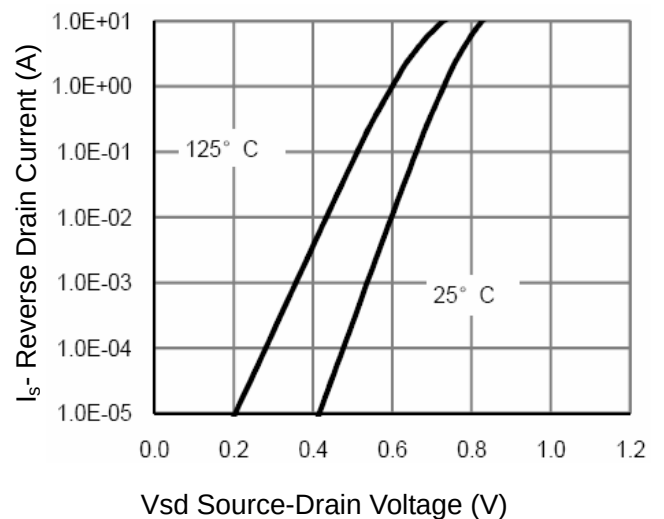


Figure 6 Source- Drain Diode Forward

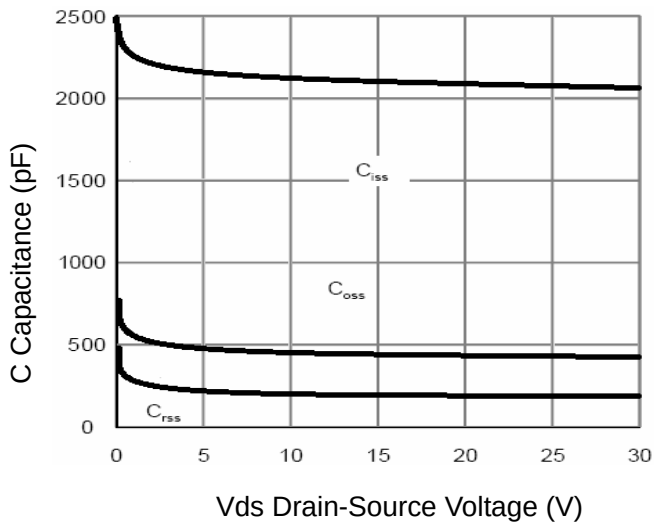


Figure 7 Capacitance vs V_{ds}

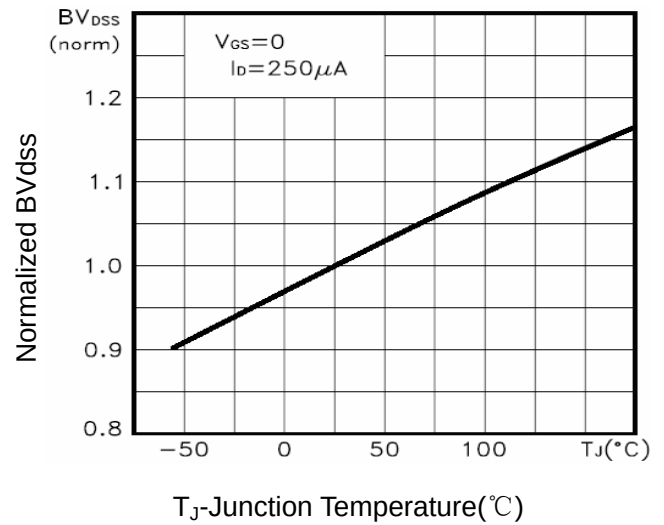


Figure 9 BV_{dss} vs Junction Temperature

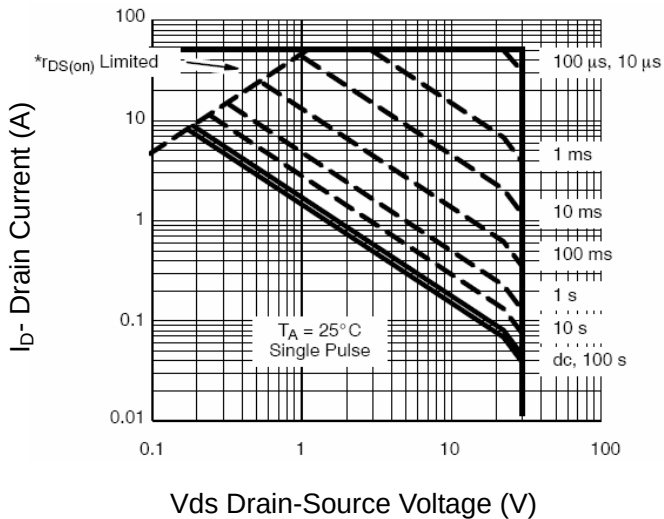


Figure 8 Safe Operation Area

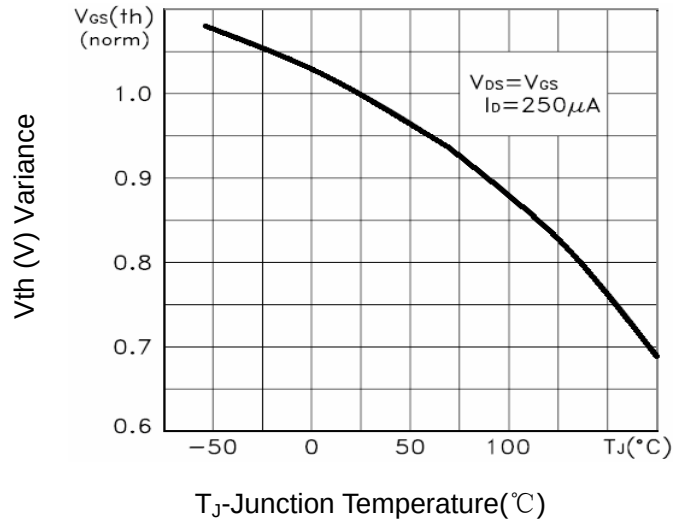


Figure 10 $V_{GS(th)}$ vs Junction Temperature

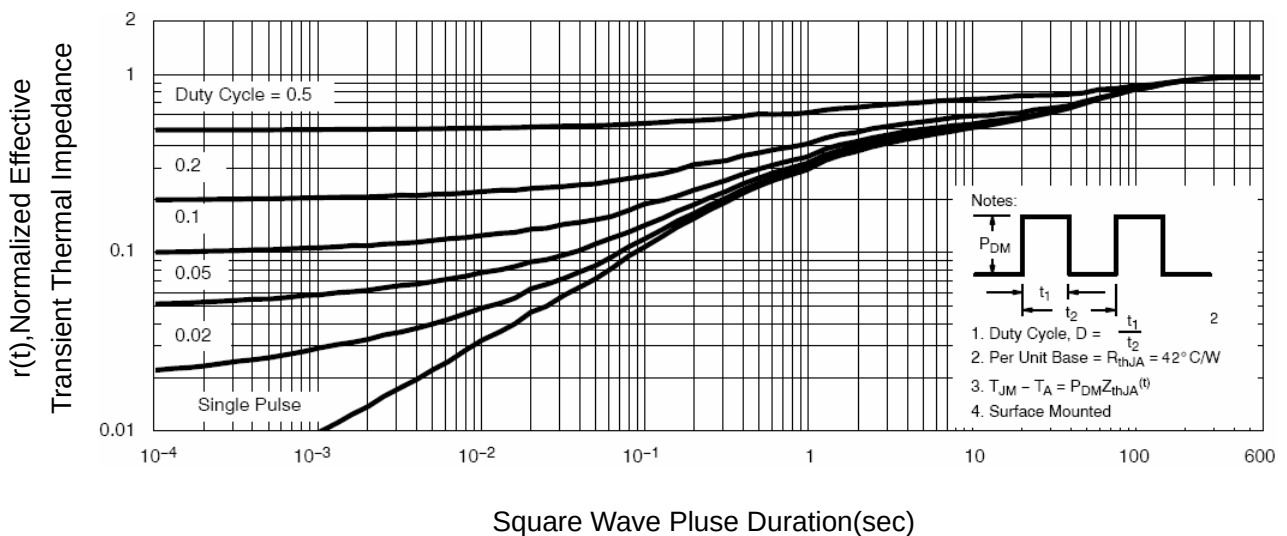
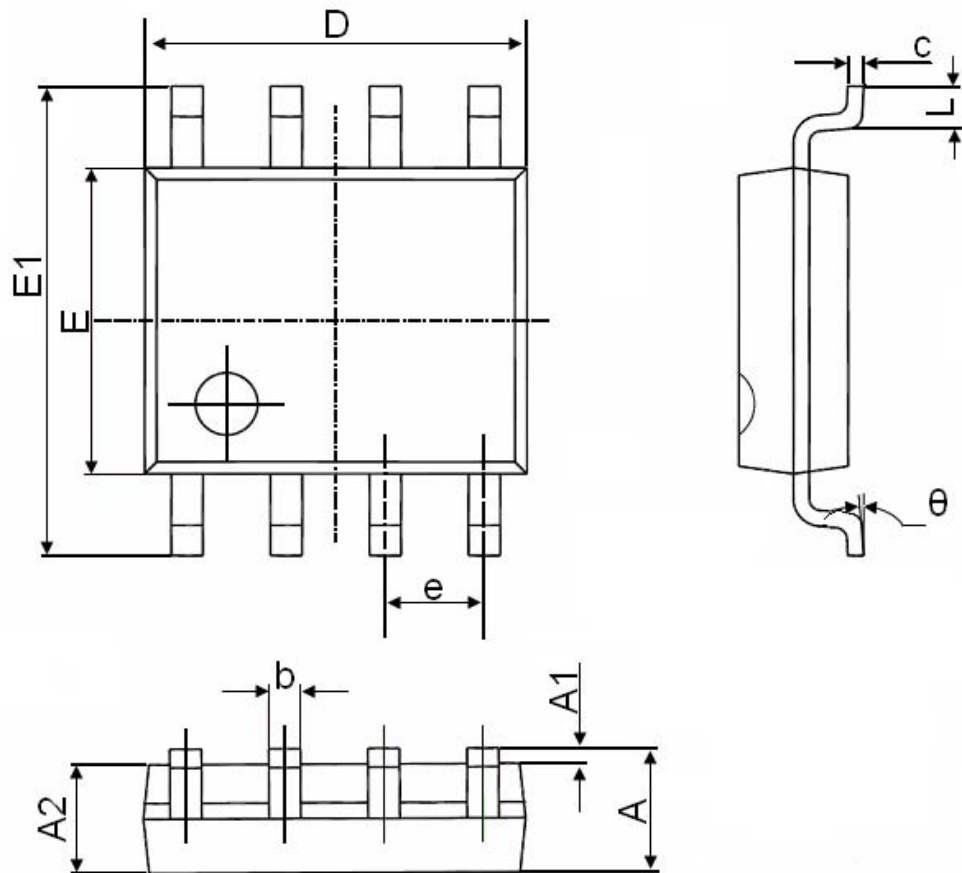


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°